

United States Patent and Trademark Office

UNITED STATES DEPARTMENT OF COMMERCE
United States Patent and Trademark Office
Address: COMMISSIONER FOR PATENTS
P.O. Box 1450
Alexandria, Virginia 22313-1450
www.usplo.gov

APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.	
10/785,666	02/23/2004	Raymond Lee Lavoie JR.	03012US	2681	
75	90 02/25/2005		EXAMINER		
Rohm and Haas Electronic,			MULLER,	MULLER, BRYAN R	
Materials CMP Holdings, Inc. Suite 1300			ART UNIT	PAPER NUMBER	
1105 North Mar	rket Street .	3723			
Wilmington, D	E 19899	DATE MAILED: 02/25/2005			

Please find below and/or attached an Office communication concerning this application or proceeding.

		Application No.	Applicant(s)				
Office Action Summary		10/785,666	LAVOIE ET AL.				
		Examiner	Art Unit				
		Bryan R Muller	3723				
Period fo	The MAILING DATE of this communication ap or Reply	pears on the cover sheet with th	e correspondence ad	ldress			
THE - External after - If the - If NO - Failu Any I	ORTENED STATUTORY PERIOD FOR REPL MAILING DATE OF THIS COMMUNICATION. nsions of time may be available under the provisions of 37 CFR 1. SIX (6) MONTHS from the mailing date of this communication. period for reply specified above is less than thirty (30) days, a replayer of or reply is specified above, the maximum statutory period reto reply within the set or extended period for reply will, by statuted the provided by the Office later than three months after the mailing patent term adjustment. See 37 CFR 1.704(b).	136(a). In no event, however, may a reply by within the statutory minimum of thirty (30) will apply and will expire SIX (6) MONTHS e, cause the application to become ABAND	e timely filed days will be considered timel from the mailing date of this control (35 U.S.C. § 133).				
Status							
1)⊠	Responsive to communication(s) filed on 23 F	ebruary 2004.					
·		s action is non-final.					
3)□	, 						
Dispositi	on of Claims						
5)□ 6)⊠	4) ☐ Claim(s) 1-10 is/are pending in the application. 4a) Of the above claim(s) is/are withdrawn from consideration. 5) ☐ Claim(s) is/are allowed. 6) ☐ Claim(s) 1-10 is/are rejected. 7) ☐ Claim(s) 1 and 7 is/are objected to. 8) ☐ Claim(s) are subject to restriction and/or election requirement.						
Applicati	ion Papers						
9)[The specification is objected to by the Examin	er.		-			
10)☐ The drawing(s) filed on is/are: a)☐ accepted or b)☐ objected to by the Examiner.							
	Applicant may not request that any objection to the drawing(s) be held in abeyance. See 37 CFR 1.85(a).						
Replacement drawing sheet(s) including the correction is required if the drawing(s) is objected to. See 37 CFR 1.121(d). 11) The oath or declaration is objected to by the Examiner. Note the attached Office Action or form PTO-152.							
Priority u	ınder 35 U.S.C. § 119						
 12) Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f). a) All b) Some * c) None of: 1. Certified copies of the priority documents have been received. 2. Certified copies of the priority documents have been received in Application No. 3. Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)). * See the attached detailed Office action for a list of the certified copies not received. 							
Attachmen	t(s)						
	e of References Cited (PTO-892)	4) Interview Summ					
3) 🛛 Infor	e of Draftsperson's Patent Drawing Review (PTO-948) mation Disclosure Statement(s) (PTO-1449 or PTO/SB/08 r No(s)/Mail Date	Paper No(s)/Ma 5) Notice of Inform 6) Other:	ul Date nal Patent Application (PT0	O-152)			

Application/Control Number: 10/785,666 Page 2

Art Unit: 3723

DETAILED ACTION

Claim Objections

- 1. Claim 1 is objected to because of the following informalities: The phrase, "ratio of thermoplastic polymer" in lines 4 and 5 should be "ratio of the thermoplastic polymer".

 Appropriate correction is required.
- Claim 7 is objected to because of the following informalities: The phrase, "ratio
 of thermoplastic polymer" in line 11 should be "ratio of the thermoplastic polymer".
 Appropriate correction is required

Claim Rejections - 35 USC § 112

- 3. The following is a quotation of the second paragraph of 35 U.S.C. 112:
 The specification shall conclude with one or more claims particularly pointing out and distinctly claiming the subject matter which the applicant regards as his invention.
- 4. Claim 1 recites the limitation "the non-ferrous interconnect" in lines 5 and 6. There is insufficient antecedent basis for this limitation in the claim.
- 5. Claim 7 recites the limitation "the non-ferrous interconnect" in line 12. There is insufficient antecedent basis for this limitation in the claim.

Claim Rejections - 35 USC § 103

6. The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

Art Unit: 3723

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.

Page 3

- 7. Claim1-10 rejected under 35 U.S.C. 103(a) as being unpatentable over Tsuchiya et al (Pub. No. 2002/0035872) in view of Choi et al (Pub. No. 2003/0139127).
- 8. In reference to claim 1, Tsuchiya discloses a chemical mechanical polishing (CMP) slurry (CMP process commonly used for polishing semiconductor substrates) that comprises a thickener in an amount of 0.001-0.05 wt% that may be any of a group of polymers including Polyvinylpyrrolidone (PVP) or (thermoplastic) polyvinyl alcohol (PVA). Choi discloses a capsulated abrasive composition (a slurry for use in CMP polishing) that comprises a binder (similar to a thickener) that is preferably PVA (paragraphs 22 and 32), silica as an abrasive, and also provides PVP in an amount of 1-10 wt% to improve the cohesiveness of the abrasives (paragraph 36), which is desirable to keep the abrasives closely grouped and adherent to the substrate to be polished to provide an consistent uniform polish. Therefore it would have been obvious to on e of ordinary skill in the art at the time the invention was made to provide the Tsuchiya slurry with 0.001-0.05 wt% PVA as a thickener and 1-10 wt% PVP to further improve cohesiveness of the abrasives, as taught by Choi. It further would have been obvious that varying the weight ratio of the PVA and PVP would control the removal rate of the semiconductor substrate because any change in the weight ratio of the two elements would alter the thickness of the slurry and the cohesiveness of the abrasives, which would inherently have an effect on the removal rate. The ranges provided are competent rejections based on MPEP § 2131.03 [R-2] - PRIOR ART WHICH TEACHES

Page 4

Art Unit: 3723

A RANGE WITHIN, OVERLAPPING, OR TOUCHING THE CLAIMED RANGE
ANTICIPATES IF THE PRIOR ART RANGE DISCLOSES THE CLAIMED RANGE
WITH "SUFFICIENT SPECIFICITY".

- 9. In reference to claim 2, the thermoplastic in the slurry of Tsuchiya is PVA.
- 10. In reference to claim 3, Tsuchiya discloses that the slurry comprises a polishing material, which may be silica (paragraph 27) in an amount of 0.1-50 wt% and more preferably 1-10 wt% (paragraph 29).
- 11. In reference to claim 4, Tsuchiya discloses that the molecular weight of the thickener (PVA) is in the range of 10,000-5,000,000 and more preferably 50,000-2,000,000, which would produce a range of weight average molecular weight that would overlap the claimed range of 1,000-1,000,000 grams pre mole. It would have been obvious that the degree of hydrolyzation of the PVA would be at least 20 mole percent because the PVA will be within a fluid mixture comprising a large majority of water (paragraph 26) based on the composition percentages provided for other contents of the slurry.
- 12. In reference to claim 5, it would be obvious that the PVP should have a similar molecular weight as the PVA to prevent dishing or erosion and provide an adequate polishing rate as taught by Tsuchiya (paragraph 43).
- 13. In reference to claim 6, the percentage ranges of PVP and PVA that will be present in the slurry provide a possible ratio range of 10,000:1 (10%:0.001%) to 20:1 (1%:0.05%), which is overlaps the claimed range (see MPEP § 2131.03 [R-2]).

Art Unit: 3723

14. In reference to claim 7, Tsuchiya discloses a polishing composition comprising 0.001-.05 wt% PVA (within claimed range), 0.0001-5 wt% (within claimed range) benzotriazole as an (corrosion inhibitor) antioxidant (paragraphs 50 and 51), 0.01-5 wt% (within claimed range) citric acid as a (complexing agent) oxidation aid (paragraphs 44-48), 0.01-15% (overlapping claimed range) hydrogen peroxide as an oxidizer (paragraphs 30 and 31), and 0.1-50 wt% and more preferably 1-10 wt% silica abrasive, as discussed supra, with a pH in the range of 3-9 or more preferably 4-8 (overlapping claimed range, paragraph 52). As discussed supra, it would have been obvious to include PVP in a range of 1-10% (overlapping range) and it would have been obvious that varying the weight ratios of the PVP and PVA will control the removal rate. It will further be obvious that the ranges discloses for the molecular weights of the PVP and PVA will provide ranges of weight average molecular weights that would overlap or touch the claimed ranges.

Page 5

15. In reference to claim 8, in view of the obvious alteration to the slurry of Tsuchiya in view of the teachings of Choi, as discussed supra, it would be obvious to use the modified slurry in the method disclosed by Tsuchiya, which provides the steps of applying a polishing composition (modified) to a semiconductor substrate and polishing the semiconductor substrate at a given pad pressure and it again would have been obvious that varying the weight ratios of the PVP and PVA would control the removal rate. Tsuchiya discloses an example wherein the pad pressure is 27.6 kPa but it would have been obvious to one of ordinary skill in the art at the time the invention was made to vary the polishing pad pressure in order to achieve a desired removal rate.

Art Unit: 3723

16. In reference to claim 9, it would have been obvious that the variation of the weight ratio of PVP and PVA, pad pressure, polishing speed, and slurry supply rate would be able to provide a removal rate within the range of 150 Angstroms/min or less.

Page 6

17. In reference to claim 10, Tsuchiya discloses a removal rate of 400-1,500 nm/min, which is equivalent to 4,000-15,000 Angstroms/min, which falls within the claimed range of 150 Angstroms/min or more. It further would have been obvious that the variation of the weight ratio of PVP and PVA, pad pressure, polishing speed, and slurry supply rate would be able to provide a removal rate within the range of 150 Angstroms/min or more.

Conclusion

18. The prior art made of record and not relied upon is considered pertinent to applicant's disclosure. Kurata (2003/0219982) discloses a CMP slurry with PVP or PVA and teaches a range of weight average molecular weight similar to the claimed ranges and Sachan (6,616,717 and 6,699,299), Wake (6,436,811 and 2002/0037642), Thomas (2002/0019202), Ishibashi (2003/0121214), Dauguet (4,222,747), Sasaki (5,352,277), Costas (6,443,812) and Tsuchiya (6,530,968 and 2001/0005009) all disclose polishing compositions with either PVA, PVP or both and posses other similarities to the claimed composition.

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Bryan R Muller whose telephone number is (571) 272-4489. The examiner can normally be reached on M-Th and every other Friday.

Art Unit: 3723

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Joseph J Hail III can be reached on (571) 272-4485. The fax phone number for the organization where this application or proceeding is assigned is 703-872-9306.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

BRM **SKN** 2/17/2005

Joseph J. Hail, III Supervisory Patent Examiner Technology Center 3700

l O. Hale

Page 7